2SB955(K)

Silicon PNP Triple Diffused

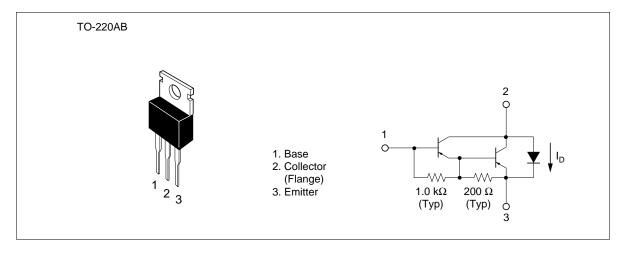
HITACHI

ADE-208-863 (Z) 1st. Edition Sep. 2000

Application

Power switching complementary pair with 2SD1126(K)

Outline





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Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	-120	V
Collector to emitter voltage	V _{CEO}	-120	V
Emitter to base voltage	V_{EBO}	-7	V
Collector current	I _c	-10	A
Collector peak current	I _{C(peak)}	– 15	A
C to E diode forward current	I _D *1	10	A
Collector power dissipation	P _c *²	50	W
Junction temperature	Tj	150	°C
Storage temperature	Tstg	-55 to +150	°C

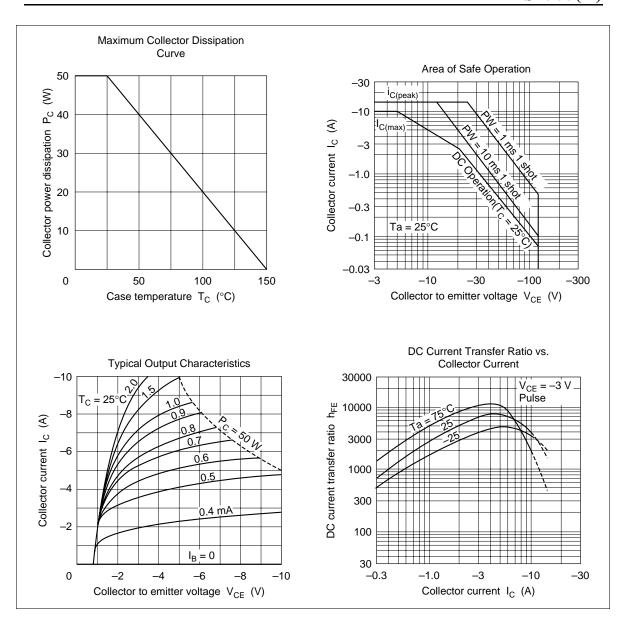
Notes: 1. Value at $T_c = 25^{\circ}C$

2. $PW \le 1 \text{ ms } 1 \text{ shot}$

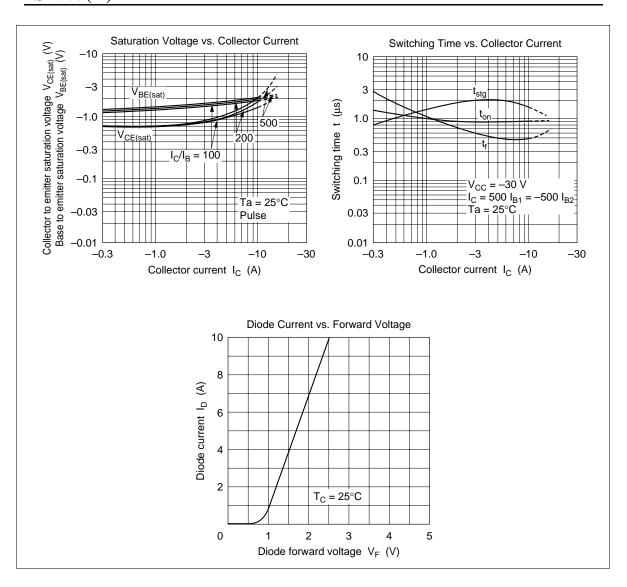
Electrical Characteristics ($Ta = 25^{\circ}C$)

Item	Symbol	Min	Тур	Max	Unit	Test conditions
Collector to emitter breakdown voltage	$V_{(BR)CEO}$	-120	_	_	V	$I_{\rm C}$ = -25 mA, $R_{\rm BE}$ = ∞
Emitter to base breakdown voltage	$V_{(BR)EBO}$	- 7	_	_	V	$I_{\rm E} = -200 \text{ mA}, I_{\rm C} = 0$
Collector cutoff current	I _{CBO}	_	_	-100	μΑ	$V_{CB} = -120 \text{ V}, I_{E} = 0$
	I _{CEO}	_	_	-10	μΑ	V _{CE} = −100 V, R _{BE} = ∞
DC current transfer ratio	h_{FE}	1000	_	20000		$V_{CE} = -3 \text{ V}, I_{C} = -5 \text{ A}^{*1}$
Collector to emitter saturation	V _{CE(sat)1}	_	_	-1.5	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	V _{CE(sat)2}	_	_	-3.0	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
Base to emitter saturation	$V_{\text{BE}(\text{sat})1}$	_	_	-2.0	V	$I_{\rm C} = -5 \text{ A}, I_{\rm B} = -10 \text{ mA}^{*1}$
voltage	V _{BE(sat)2}	_	_	-3.5	V	$I_{\rm C} = -10 \text{ A}, I_{\rm B} = -0.1 \text{ A}^{*1}$
C to E diode forward voltage	V _D	_	_	3.0	V	I _D = 10 A*1
Turn on time	t _{on}	_	8.0	_	μs	V _{cc} = -30 V
Turn off time	t _{off}	_	4.0	_	μs	$I_{\rm C} = -5 \text{ A}, I_{\rm B1} = -I_{\rm B2} = -10 \text{ mA}$

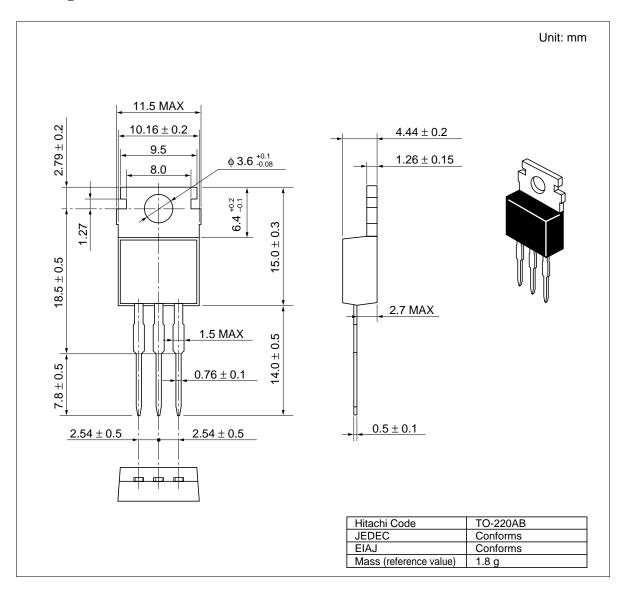
Note: 1. Pulse test



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Package Dimensions



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